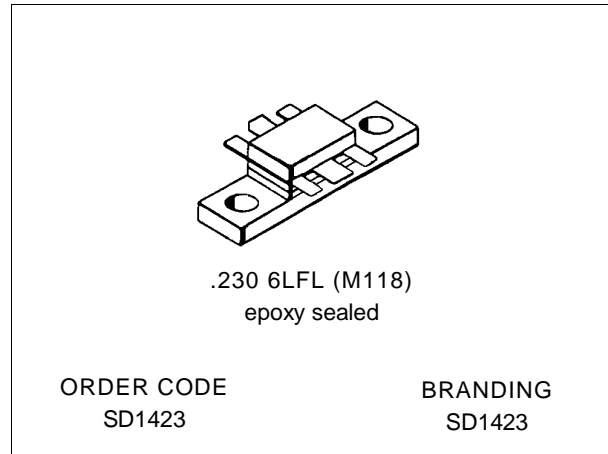


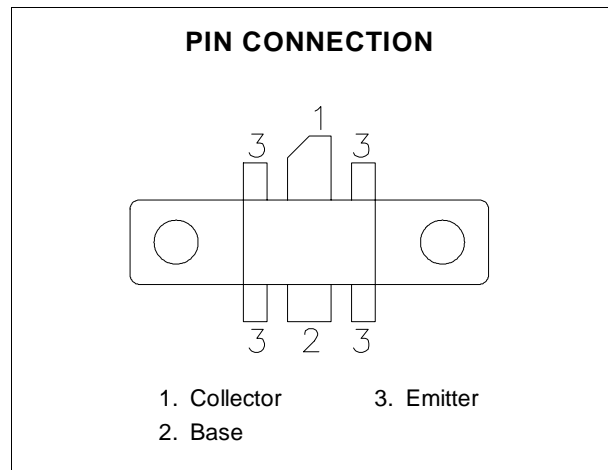
RF & MICROWAVE TRANSISTORS 800-960MHz BASE STATION APPLICATIONS

- 800 - 960 MHz
- 24 VOLTS
- EFFICIENCY 50%
- COMMON EMITTER
- GOLD METALLIZATION
- CLASS AB LINEAR OPERATION
- P_{OUT} = 15 W MIN. WITH 8.0 dB GAIN



DESCRIPTION

The SD1423 is a gold metallization epitaxial silicon NPN planar transistor using diffused emitter ballast resistors for high linearity Class AB operation for cellular base station applications. The SD1423 is designed as a medium power output device or as the driver for the SD1424.



ABSOLUTE MAXIMUM RATINGS (T_{case} = 25°C)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	48	V
V _{CEO}	Collector-Emitter Voltage	25	V
V _{CES}	Collector-Emitter Voltage	45	V
V _{EBO}	Emitter-Base Voltage	3.5	V
I _C	Device Current	2.5	A
P _{DISS}	Power Dissipation	29	W
T _J	Junction Temperature	+200	°C
T _{STG}	Storage Temperature	- 65 to +150	°C

THERMAL DATA

R _{TH(j-c)}	Junction-Case Thermal Resistance	6	°C/W
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ELECTRICAL SPECIFICATIONS ($T_{case} = 25^{\circ}C$)

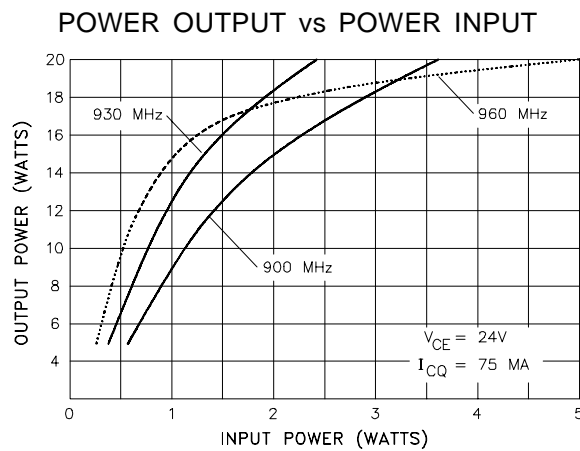
STATIC

Symbol	Test Conditions		Value			Unit
			Min.	Typ.	Max.	
BV_{CBO}	$I_C = 50mA$	$I_E = 0mA$	48	50	—	V
BV_{CEO}	$I_C = 20mA$	$I_B = 0mA$	25	30	—	V
BV_{EBO}	$I_E = 5mA$	$I_C = 0mA$	3.5	4.0	—	V
I_{CBO}	$V_{CB} = 24V$	$I_E = 0mA$	—	—	1.0	mA
h_{FE}	$V_{CE} = 10V$	$I_C = 100mA$	20	—	100	—

DYNAMIC

Symbol	Test Conditions			Value			Unit
				Min.	Typ.	Max.	
P_{OUT}	$f = 960\text{ MHz}$	$V_{CC} = 24\text{ V}$	$I_{CQ} = 75\text{ mA}$	15	—	—	W
P_G	$f = 960\text{ MHz}$	$V_{CC} = 24\text{ V}$	$I_{CQ} = 75\text{ mA}$	8	—	—	dB
η_C	$f = 960\text{ MHz}$	$V_{CC} = 24\text{ V}$	$I_{CQ} = 75\text{ mA}$	45	50	—	%
C_{OB}	$f = 1\text{ MHz}$	$V_{CB} = 24V$		—	20	24	pF

TYPICAL PERFORMANCE

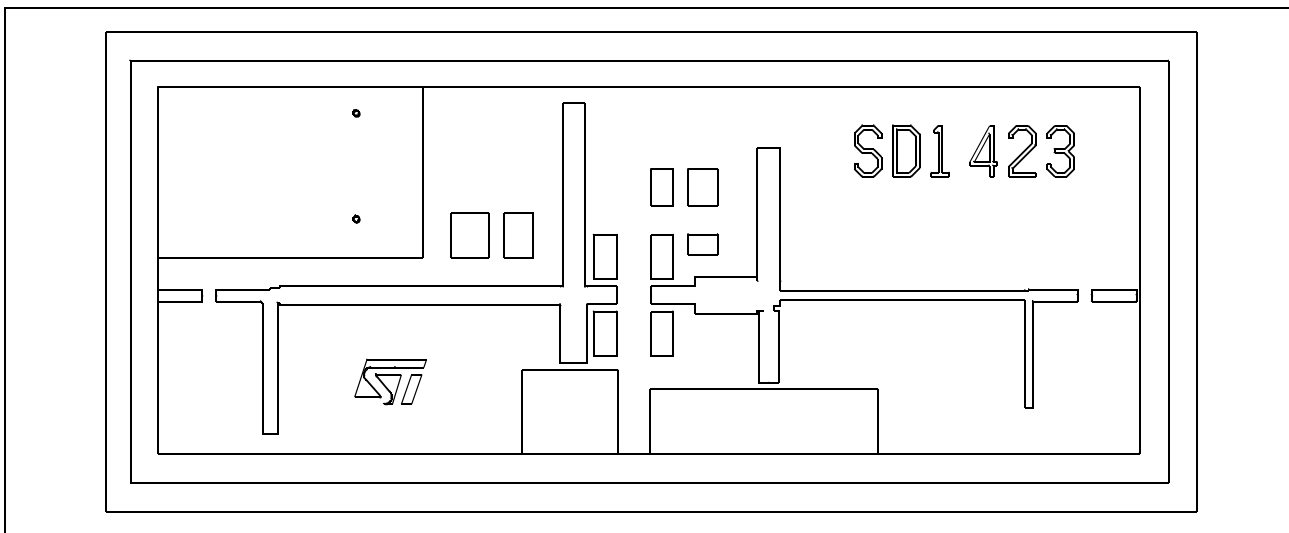


IMPEDANCE DATA

FREQ.	$Z_{IN} (\Omega)$	$Z_{CL} (\Omega)$
900 MHz	$1.30 + j 1.98$	$3.99 + j 5.55$
930 MHz	$1.42 + j 2.31$	$3.18 + j 4.97$
960 MHz	$1.45 + j 2.62$	$2.96 + j 4.07$

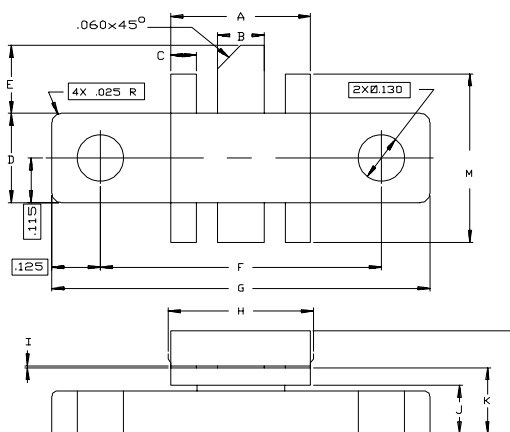
$P_{OUT} = 15\text{ W}$
 $V_{CE} = 75\text{ mA}$
 $I_{CQ} = 24\text{ V}$

TEST CIRCUIT LAYOUT



PACKAGE MECHANICAL DATA

Ref.: UDCS Doc. No.1010941 rev. B



SGS-THOMSON MICROELECTRONICS			CONT'D	
	MINIMUM Inches/mm	MAXIMUM Inches/mm	MINIMUM Inches/mm	MAXIMUM Inches/mm
A	.355/9,02	.365/9,27	K	.160/4,06
B	.115/2,92	.125/3,18	L	.250/6,35
C	.060/1,52	.070/1,78	M	.420/10,67
D	.225/5,72	.235/5,97		
E	.150/3,81	.170/4,32		
F	.720/18,29	.730/18,54		
G	.970/24,64	.980/24,89		
H	.355/9,02	.365/9,27		
I	.004/0,10	.006/0,15		
J	.120/3,05	.130/3,30		

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